

15V NPN LOW SATURATION TRANSISTOR
Features and Benefits

- $BV_{CEO} > 15V$
- $I_C = 4.5A$ Continuous Collector Current
- Low Saturation Voltage (100mV max @ 1A)
- $R_{SAT} = 45 m\Omega$ for a low equivalent On-Resistance
- h_{FE} specified up to 12A for high current gain hold up
- Low profile 0.6mm high package for thin applications
- $R_{\theta JA}$ efficient, 60% lower than SOT23
- 4mm² footprint, 50% smaller than SOT23
- **Lead-Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

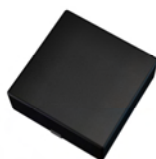
Mechanical Data

- Case: DFN2020B-3
- Case Material: Molded Plastic. "Green" Molding Compound.
- Terminals: Pre-Plated NiPdAu leadframe.
- Nominal Package Height: 0.6mm
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.01 grams (approximate)

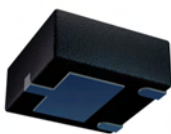
Applications

- MOSFET Gate Driving
- DC-DC Converters
- Charging Circuits
- Motor Control
- Power switch

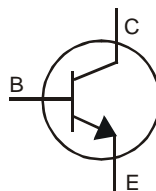
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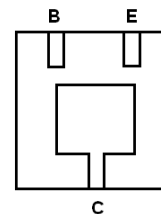
Top View



Bottom View



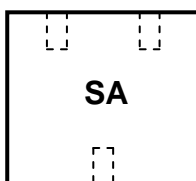
Device Symbol


 Bottom View
Pin-Out

Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN617MATA	SA	7	8	3000

Notes: 1. No purposefully added lead.
 2. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>.

Marking Information
www.DataSheet4U.com


Top View

SA = Product Type Marking code

Maximum Ratings @T_A = 25°C unless otherwise specified

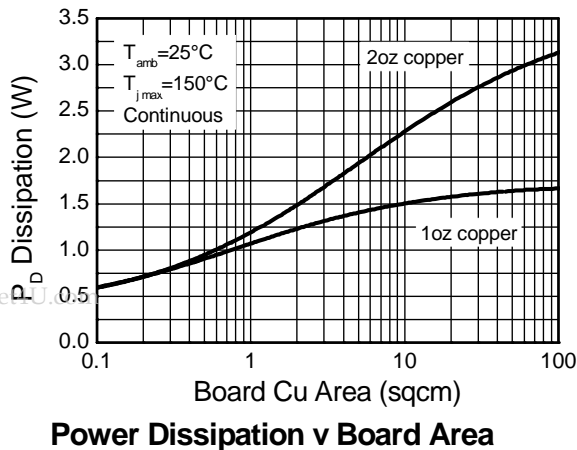
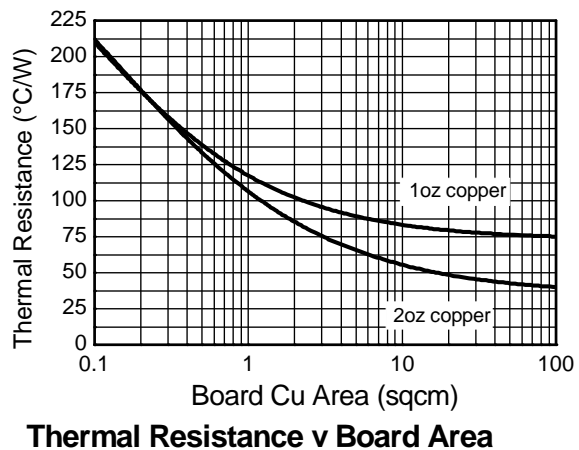
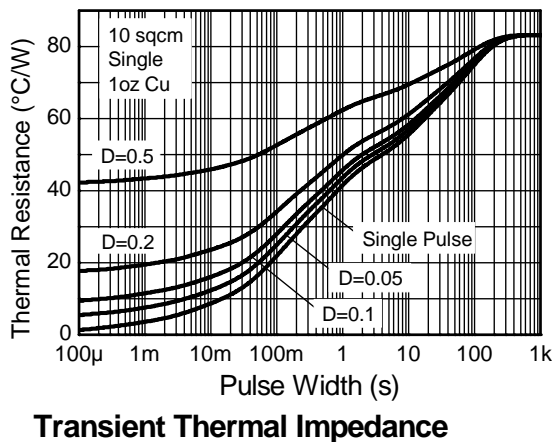
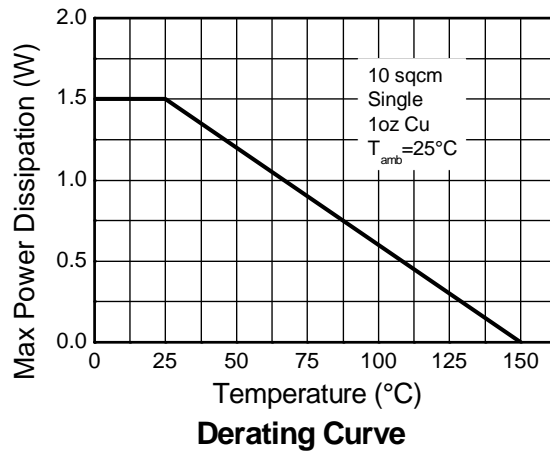
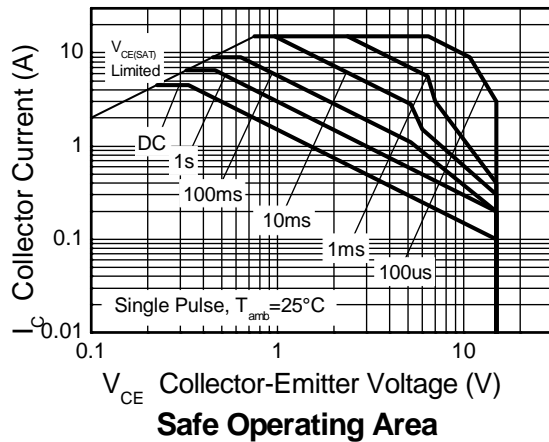
Characteristic		Symbol	Value	Unit
Collector-Base Voltage		V _{CBO}	40	V
Collector-Emitter Voltage		V _{CEO}	15	
Emitter-Base Voltage		V _{EBO}	7	
Peak Pulse Current		I _{CM}	15	A
Continuous Collector Current	(Note 3)	I _C	4.5	
	(Note 4)		5	
Base Current		I _B	1	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 3)	P _D	1.5	W
	(Note 4)		12	
Linear Derating Factor	(Note 3)	R _{θJA}	2.45	mW/°C
	(Note 4)		19.6	
Thermal Resistance, Junction to Ambient	(Note 3)	R _{θJA}	83	°C/W
	(Note 4)		51	
Thermal Resistance, Junction to Lead	(Note 5)	R _{θJL}	16.8	°C
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	

- Notes:
3. For a device surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
 4. Same as note (3), except the device is measured at t ≤ 5 sec.
 5. For a single device, thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics

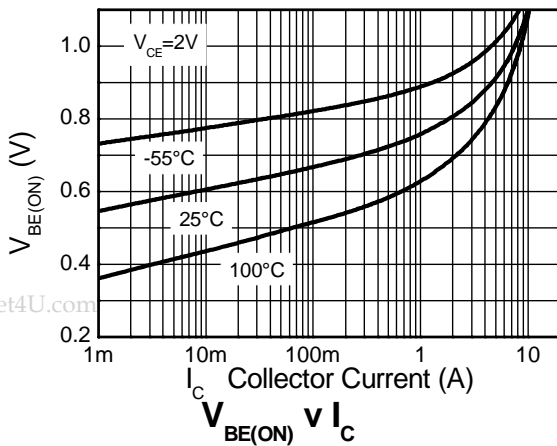
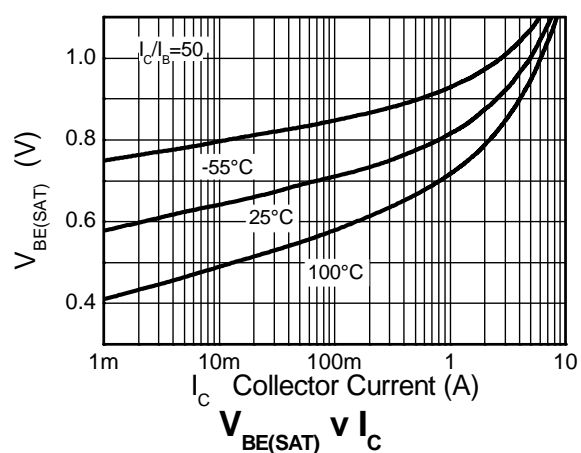
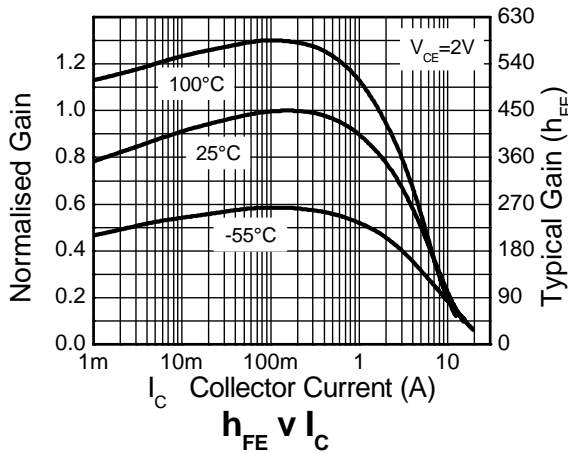
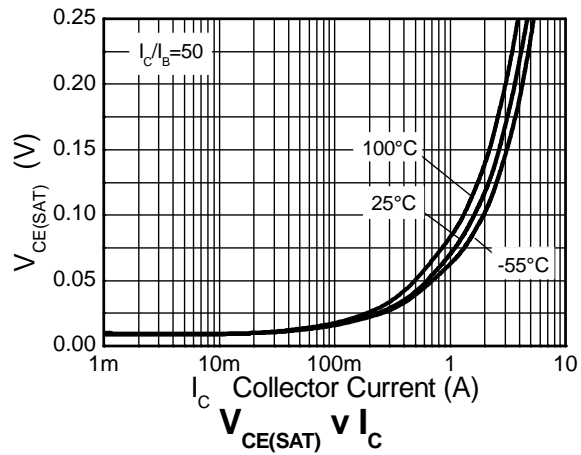
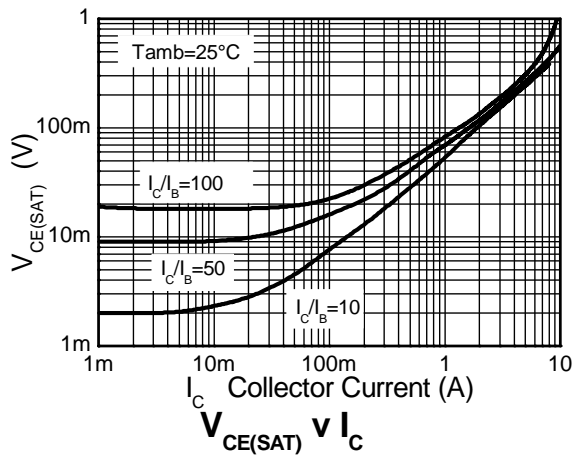


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	70	-	V	I _C = 100 µA
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	15	18	-	V	I _C = 10 mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	-	V	I _E = 100 µA
Collector Cutoff Current	I _{CBO}	-	-	100	nA	V _{CB} = 30V
Emitter Cutoff Current	I _{EBO}	-	-	100	nA	V _{EB} = 6V
Collector Emitter Cutoff Current	I _{CES}	-	-	100	nA	V _{CES} = 12V
Static Forward Current Transfer Ratio (Note 6)	h _{FE}	200	415	-	-	I _C = 10mA, V _{CE} = 2V
		300	450	-		I _C = 200mA, V _{CE} = 2V
		200	320	-		I _C = 3A, V _{CE} = 2V
		150	240	-		I _C = 5A, V _{CE} = 2V
		-	80	-		I _C = 12A, V _{CE} = 2V
Collector-Emitter Saturation Voltage (Note 6)	V _{CE(sat)}	-	8	14	mV	I _C = 0.1A, I _B = 10mA
		-	70	100		I _C = 1A, I _B = 10mA
		-	165	200		I _C = 3A, I _B = 50mA
		-	240	310		I _C = 4.5A, I _B = 50mA
		-	200	-		I _C = 4.5A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 6)	V _{BE(on)}	-	0.88	0.96	V	I _C = 4.5A, V _{CE} = 2V
Base-Emitter Saturation Voltage (Note 6)	V _{BE(sat)}	-	0.94	1.05	V	I _C = 4.5A, I _B = 50mA
Output Capacitance	C _{obo}	-	30	40	pF	V _{CB} = 10V, f = 1MHz
Transition Frequency	f _T	80	120	-	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-On Time	t _{on}	-	120	-	ns	V _{CC} = 10V, I _C = 1A
Turn-Off Time	t _{off}	-	160	-	ns	I _{B1} = I _{B2} = 10mA

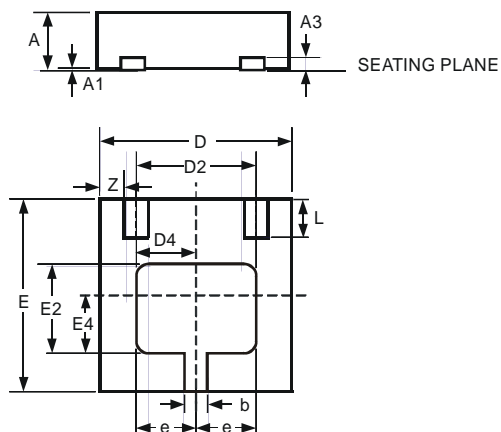
Notes: 6. Measured under pulsed conditions. Pulse width ≤ 300 µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics



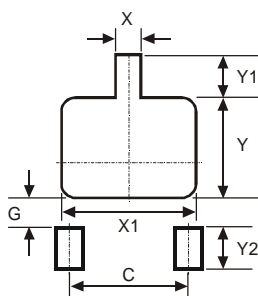
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Package Outline Dimensions



DFN2020B-3			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.02
A3	—	—	0.152
b	0.20	0.30	0.25
D	1.95	2.075	2.00
D2	1.22	1.42	1.32
D4	0.56	0.76	0.66
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.79	0.99	0.89
E4	0.48	0.68	0.58
L	0.25	0.35	0.30
Z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	1.30
G	0.24
X	0.35
X1	1.52
Y	1.09
Y1	0.47
Y2	0.50

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